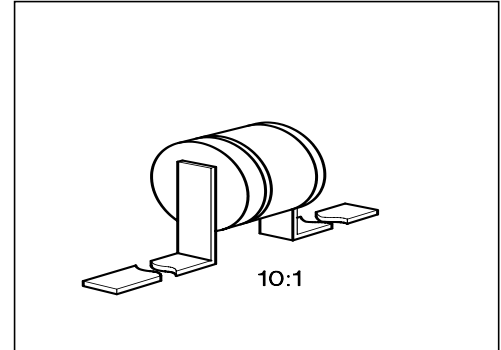
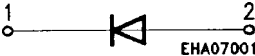


## Silicon PIN Diode

**BXY 44K**

- Microwave attenuator diode
- Linear RF characteristic



Type	Marking	Ordering Code	Pin Configuration	Package <sup>1)</sup>
BXY 44K	–	Q62702-X148	Cathode: black dot, heat sink 	T1

### Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	$V_R$	200	V
Forward current	$I_F$	0.5	A
Peak forward current, $t_p = 1 \mu\text{s}$	$I_{FRM}$	20	
Total power dissipation	$P_{tot}$	600	mW
Junction temperature	$T_j$	175	°C
Storage temperature range	$T_{stg}$	– 65 ... + 150	
Operating temperature range	$T_{op}$	– 65 ... + 150	

<sup>1)</sup> For detailed information see chapter Package Outlines.

## Electrical Characteristics

at  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Breakdown voltage $I_R = 10\text{ }\mu\text{A}$	$V_{(BR)}$	200	–	–	V
Forward voltage $I_R = 100\text{ mA}$	$V_F$	–	–	1	
Reverse current $V_R = 100\text{ V}$	$I_R$	–	–	10	nA
Storage time $I_F = 10\text{ mA}$ , $V_R = 10\text{ V}$	$t_s$	–	50	–	ns
Diode capacitance $V_R = 50\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	–	–	0.4	pF
Case capacitance	$C_C$	–	0.1	–	
Charge carrier life time $I_F = 10\text{ mA}$ , $I_R = 6\text{ mA}$	$\tau_L$	–	0.5	–	$\mu\text{s}$
Forward resistance $f = 100\text{ MHz}$ , $I_F = 10\text{ }\mu\text{A}$ $f = 100\text{ MHz}$ , $I_F = 1\text{ mA}$ $f = 100\text{ MHz}$ , $I_F = 10\text{ mA}$	$r_f$	–	1000 25 3.5	–	$\Omega$
		–		–	
		–		–	



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